

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3384399	memory or storage	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/16 11:05
L2	781219	1 and (volatile or \$3ram or static or dynamic)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/16 11:15
L3	12	2 and (metal adj5 transistor or mosfet or mos) with floating adj gate with status	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/16 11:10
L4	2415	2 and control adj gate with well	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/16 11:17
L5	1312	2 and control adj gate with well with floating adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/16 11:18
L6	3	2 and control adj gate with well with floating adj gate with status	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/16 11:18

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Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	((memory or storage) and (volatile or \$4ram) and (mosfet or metal adj oxide) and (eeprom or electrically adj erasable) and status and control adj gate and well).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/16 11:22